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Abstract

Method for filling a contact hole and integrated circuit arrangement with contact hole

An explanation is given of a method in which a base layer (50) is deposited in a contact hole region (30) under a protective gas, which base layer contains a nitride as main constituent. After the deposition of the base layer (50), a covering layer (54) is deposited under gaseous nitrogen. An adhesion promoting layer (32) results which is simple to produce and has good electrical properties.

(Figure 4)